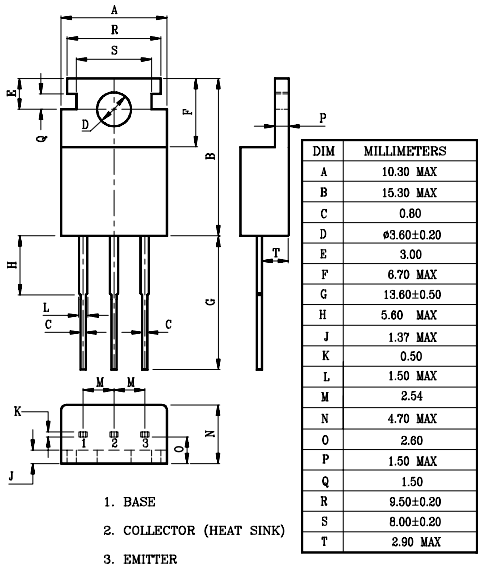
KTA968A

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

- High Transition Frequency : f_T=100MHz(Typ.).
- Complementary to KTC2238A.



DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	0.80
D	ø3.60±0.20
E	3.00
F	6.70 MAX
G	13.60±0.50
H	5.60 MAX
J	1.37 MAX
K	0.50
L	1.50 MAX
M	2.54
N	4.70 MAX
O	2.60
P	1.50 MAX
Q	1.50
R	9.50±0.20
S	8.00±0.20
T	2.90 MAX

TO-220AB

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-180	V
Collector-Emitter Voltage	V_{CEO}	-180	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	A
Emitter Current	I_E	1.5	A
Collector Power Dissipation (Tc=25℃)	P_C	25	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-160V, I_E=0	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-180	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5.0	-	-	V
DC Current Gain	h_{FE}(Note)	V_{CE}=-5V, I_C=-100mA	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-1.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA	-	-	-1.0	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-100mA	-	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	30	-	pF

Note : h_{FE} Classification O:70~140, Y:120~240